

AMENDMENTS TO THE SPECIFICATION

Please replace ¶ 68 of the published publication with the following amended paragraph:

[0068]        wherein,  $\lambda$  represents a wavelength of the incident light,  $n$  represents a refractive index of a particle,  $R$  indicates a length from a position measuring ~~measured~~ the scattered light, i.e., a length of a detector,  $\alpha$  indicates a diameter of the particle, and  $\theta$  indicates the incident angle of the light.

Please replace ¶ 83 of the published publication with the following amended paragraph:

[0083]        ~~79~~ Referring to FIG. 4 and FIGS. 5A to 5E, a PSL having a diameter of approximately 0.2  $\mu\text{m}$ , as shown in FIG. 5A, is formed in an area CL1, which has a P light PMT voltage of about 0.2 to about 0.5 and a C light PMT voltage of about 0.8 to about 1.2. A PSL having a diameter of approximately 0.5  $\mu\text{m}$ , as shown in FIG. 5B, is formed in an area CL2, which has a P light PMT voltage of about 1.3 to about 1.7 and a C light PMT voltage of about 2.4 to about 2.9. The real particles having a diameter of approximately 2.0  $\mu\text{m}$ , as shown in FIG. 5C, are formed in an area CL3, which has a P light PMT voltage of about 3.4 to about 4.0 and a C light PMT voltage of about 3.6 to about 4.0. In addition, a micro-scratch, as shown in FIGS. 5D and 5E, is formed in an area CL4, which is below a transition line and has a P light PMT of about 3.5.

Please replace ¶ 105 of the published publication with the following amended paragraph:

[0105]        The detector 140 may include a PMT. The detector 140 measures the intensity of the scattered light, i.e., the PMT voltage. The two detectors 140 are disposed on either side of the inspection spot IS at an angle of about ~~4520~~ 45° relative to the travel path of the light.

Please replace ¶ 113 of the published publication with the following amended paragraph:

[0113] According to the inspecting apparatus of the present invention, the time required for to scan a wafer is about three (3) minutes. Since the inspecting apparatus of the invention classifies the defects by scanning the wafer twice, the estimated time required for inspecting one wafer is about six (6) minutes.

Please replace ¶ 122 of the published publication with the following amended paragraph:

[0122] The first and second light sources 220 and 225 are disposed at a slant with respect to a horizontal plane, and are positioned to face each other at opposite sides of the wafer W. The first and second lights L1 and L2 emitted from the first and second light sources 220 and 225 are irradiated to the wafer W at an incident angle of about 20.degree.. The first and second light sources 220 and 225 preferably emit lasers having a wavelength of approximately 488 nm. The laser having such a wavelength is suitable to defect inspection, in particular, because the laser is stable. However, lasers or lights having other wavelengths may be used for the defect inspection. The first and second lights L1 and L2 from the first and second light sources 220 and 225, respectively, successively scan over the entire surface of the wafer W. In addition, the first and second light sources 220 and 225 are separated from each other by an angle of about ~~180~~ 180° in one embodiment. However, the first and second light sources 220 and 225 may be disposed at other angles [[,]] as well ~~about 180°~~, within the limit of having no fatal influence on the mutual functions.